

DFB20T

Diffused Junction Type Silicon Diode

2.0A Power Rectifier

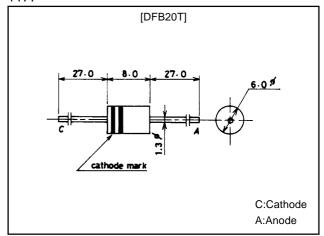
Features

- · High-speed switching use.
- \cdot Reverse recovery time $\,$ trr=0.15 μs max (B, C, E, G). $\,$ trr=0.3 μs max (J, L).
- \cdot Peak reverse voltage: V_{RM} =100 to 1000V
- · Average Rectified current I_O=2.0A

Package Dimensions

unit:mm

1177



Specifications

Absolute Maximum Ratings at Ta = 25°C

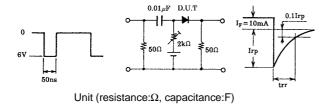
Parameter	Symbol	Conditions	DFB20TB	DFB20TC	DFB20TE	DFB20TG	Unit
Peak Reverse Voltage	V _{RM}		100	200	400	600	V
Average Recitified Current	lo	Ta=40°C	\rightarrow	\rightarrow	\rightarrow	2.0	Α
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	\rightarrow	\rightarrow	\rightarrow	120	Α
Junction Temperature	Tj		\rightarrow	\rightarrow	\rightarrow	150	°C
Storage Temperature	Tstg		\rightarrow	\rightarrow	\rightarrow	-40 to +150	°C

Parameter	Symbol	Conditions	DFB20TJ	DFB20TL		Unit
Peak Reverse Voltage	V _{RM}		800	1000		V
Average Rectified Current	Io	Ta=40°C	\rightarrow	2.0		Α
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	\rightarrow	70		Α
Junction Temperature	Tj		\rightarrow	125		°C
Storage Temperature	Tstg		\rightarrow	-40 to +150		°C

Electrical Characteristics at Ta = 25°C

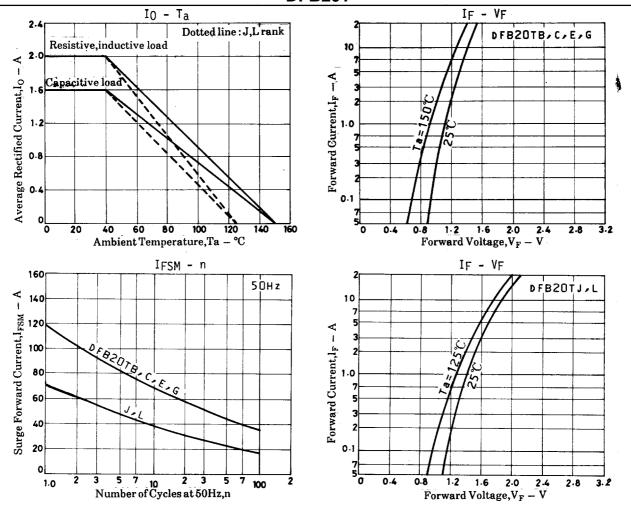
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Forward Voltage	٧F	I _F =2.0A (B, C, E, G)			1.2	V
		IF=2.0A (J, L)			1.5	V
Reverse Current	I _R	V _R :At each V _{RM}			10	μΑ
Reverse Recovery Time	trr	I _F =2mA, V _R =15V (B,C, E, G)			0.15	μs
		I _F =2mA, VR=15V (J, L)			0.3	μs

Reverse Recovery Time Test Circuit



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